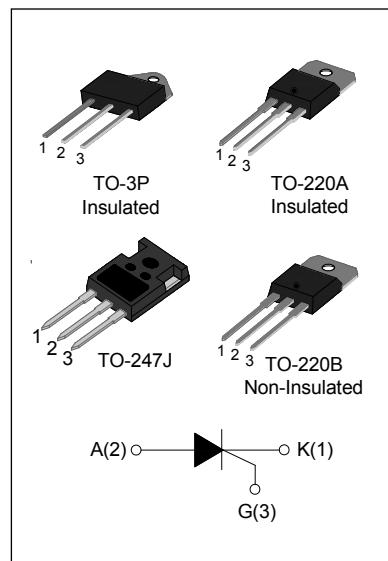




DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT1240 provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink, JCT1240Z and JCT1240A provide a rated insulation voltage of 2500 V_{RMS}, complying with UL standards (File ref: E252906).



MAIN FEATURES

Symbol	JCT1240
V _{DRM} / V _{R_{RRM}}	1200V
I _{T(RMS)}	40A
I _{GT}	≤ 60mA

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40-150	°C
Operating junction temperature range		T _j	-40-125	°C
Repetitive peak off-state voltage(T _j =25°C)		V _{DRM}	1200	V
Repetitive peak reverse voltage(T _j =25°C)		V _{R_{RRM}}	1200	V
Non repetitive surge peak Off-state voltage		V _{DSM}	V _{DRM} +100	V
Non repetitive peak reverse voltage		V _{RSM}	V _{R_{RRM}} +100	V
RMS on-state current	TO-3P(Ins) (T _C =90°C)	I _{T(RMS)}	40	A
	TO-220A(Ins) (T _C =80°C)			
	TO-247J (T _C =100°C)			
	TO-220B(Non-Ins) (T _C =85°C)			

Non repetitive surge peak on-state current (tp=10ms)	I_{TSM}	460	A
I^2t value for fusing (tp=10ms)	I^2t	1060	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	di/dt	100	$A/\mu s$
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ C$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33\Omega$	-	40	60	mA
V_{GT}		-	-	1.5	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ C R_L=3.3K\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	150	mA
I_H	$I_T=500mA$	-	-	100	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ C$	1000	-	-	$V/\mu s$

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=80A tp=380\mu s$	$T_j=25^\circ C$	1.6	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	10	μA
I_{RRM}		$T_j=125^\circ C$	4	mA

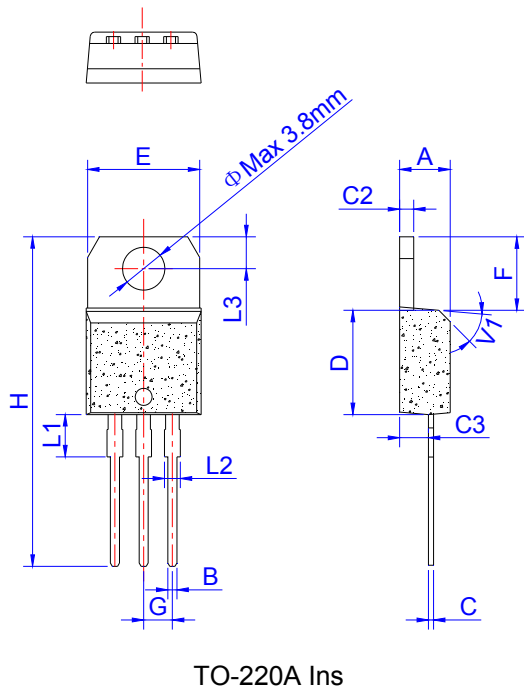
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-3P(Ins)	1.1	$^\circ C/W$
		TO-220A(Ins)	1.3	
		TO-247J	0.95	
		TO-220B(Non-Ins)	1.2	

ORDERING INFORMATION

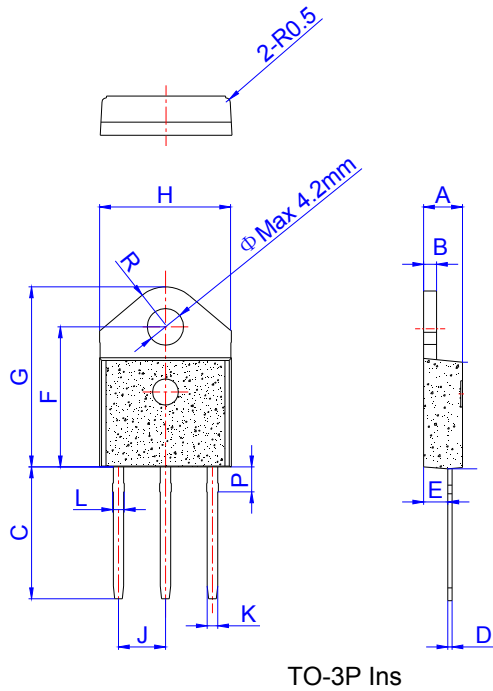
<p>JieJie Microelectronics Co.,Ltd</p>	<p>J</p>	<p>CT</p>	<p>12</p>	<p>40</p>	<p>A</p>
		<p>SCRs</p>		<p>$I_{T(RMS)}:40A$</p>	<p>A:TO-220A(Ins) B:TO-220B(Non-Ins) Z:TO-3P(Ins) SJ:TO-247J</p>
			<p>12:$V_{DRM}/V_{RRM} \geq 1200V$</p>		

PACKAGE MECHANICAL DATA

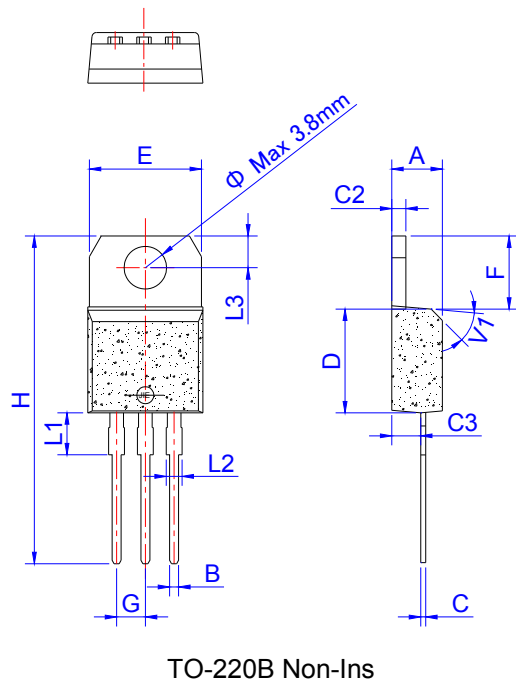


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA

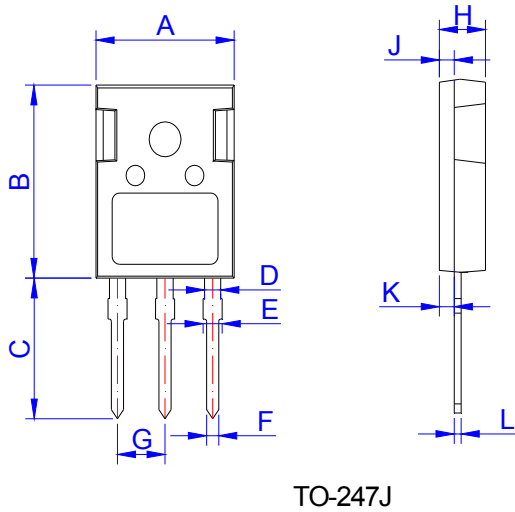


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.35		1.50	0.053		0.059
P	2.80		3.00	0.110		0.118
R		4.35			0.171	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-247J

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10	0.610	0.622	0.634
B	20.80	21.00	22.20	0.819	0.828	0.874
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G		5.44			0.214	
H	4.80	5.00	5.20	0.189	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

FIG.1 Maximum power dissipation versus RMS on-state current

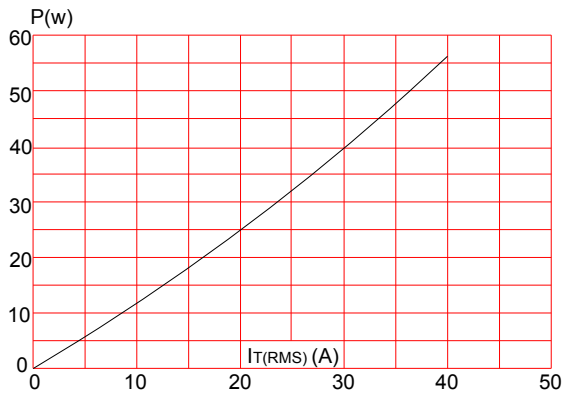


FIG.3: Surge peak on-state current versus number of cycles

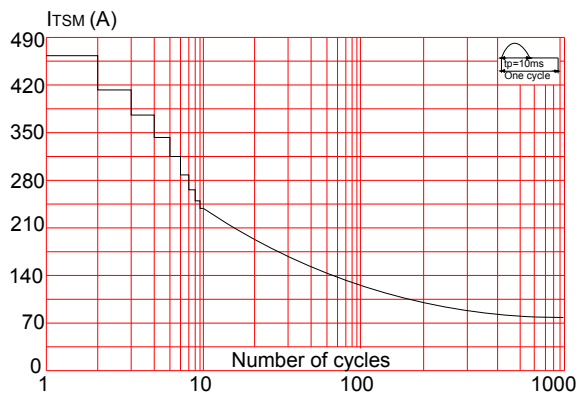


FIG.2: RMS on-state current versus case temperature

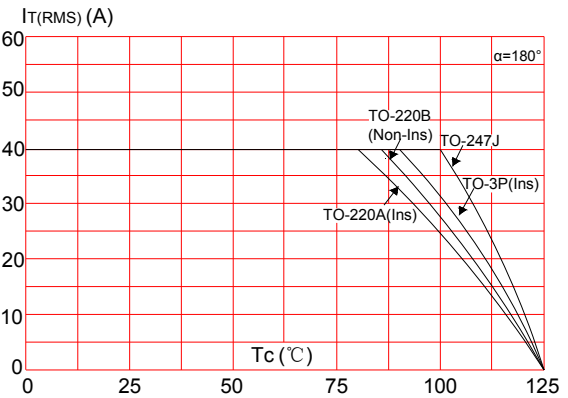


FIG.4: On-state characteristics (maximum values)

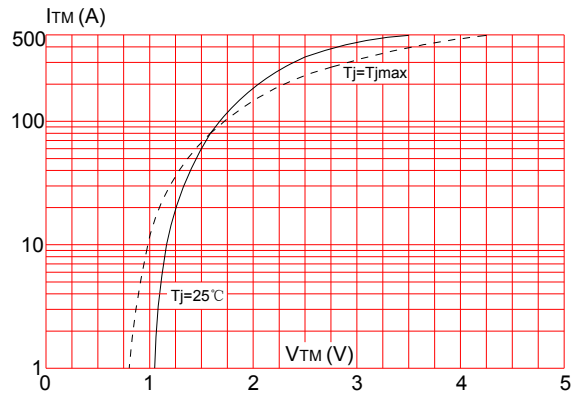


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

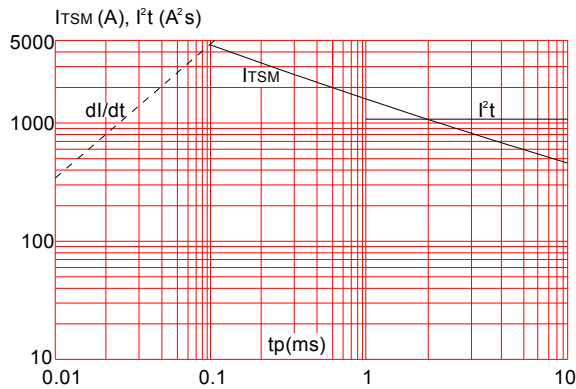
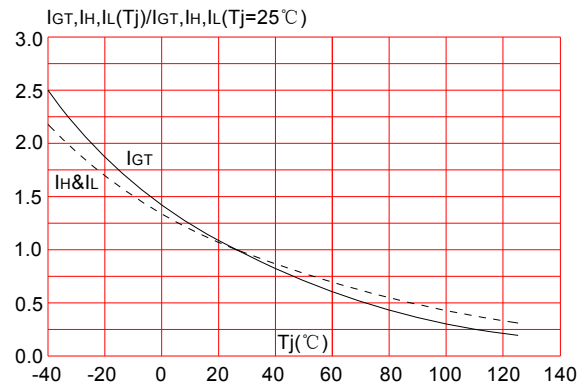



FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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